

CLAIMS

1. A light-emitting device (100) comprising a semiconductor excitation light source (102) emitting blue-violet light and a solid material illuminant (105) having an absorbent (103) for said blue-violet light containing Sm.
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2. The light-emitting device (100) according to claim 1, wherein said blue-violet light has a peak wavelength in the range of 398 to 412 nm.
- 10 3. The light-emitting device (100) according to claim 2, wherein said semiconductor excitation light source (102) emitting blue-violet light is a semiconductor laser device having an active layer of an InGaN semiconductor.
- 15 4. The light-emitting device (100) according to claim 1, wherein said solid material illuminant (105) contains Sc, Y or a typical element as cations, and contains at least one of N, O and S as anions.
5. The light-emitting device (100) according to claim 4, wherein said solid material illuminant (105) contains both N and O as anions.
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6. The light-emitting device (100) according to claim 4, wherein said solid material illuminant (105) contains at least one of nitrides of Ga, In and Al.
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7. The light-emitting device (100) according to claim 4, wherein said solid material illuminant (105) contains at least one of oxides of Y, Si, Al and Zn.

8. The light-emitting device (100) according to claim 1, wherein
said solid material illuminant (105) contains a red phosphor having a peak
wavelength in the range of 600 to 670 nm, a green phosphor having a peak wavelength
in the range of 500 to 550 nm and a blue phosphor having a peak wavelength in the
range of 450 to 480 nm.

9. The light-emitting device (100) according to claim 8, wherein
said red phosphor, said green phosphor and said blue phosphor contain rare
earth elements.

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10. The light-emitting device (100) according to claim 8, wherein
said red phosphor contains at least either Sm or Eu.